

Substitute Form PTO-1449

U.S. Department of Commerce
Patent and Trademark OfficeAttorney's Docket No.
07977-052001Application No.
08/690,747

(Modified)

**Information Disclosure Statement
by Applicant**

(Use several sheets if necessary)

Applicant
Hisashi Ohtani et alFiling Date
August 1, 1996Group Art Unit
1765

(37 CFR §1.98(b))

U.S. Patent Documents

Examiner Initial	Desig. ID	Patent Number	Issue Date	Patentee	Class	Subclass	Filing Date If Appropriate
<i>J</i>	AA	5,956,579	09/21/99	Yamazaki et al.			
<i>P</i>	AB	6,072,193	06/06/00	Ohnuma et al.			
<i>P</i>	AC	6,066,518	05/23/00	Yamazaki			
<i>T</i>	AD	5,244,819	09/14/93	Yue			
<i>ii</i>	AE	4,371,403	02/01/83	Ikubo et al.			
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						

RECEIVED

MAR 01 2001

TC 1700

Foreign Patent Documents or Published Foreign Patent Applications

Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation	
							Yes	No
<i>J</i>	AL	5-109737	April 30, 1993	Japan			X	
	AM							
	AN							
	AO							
	AP							

Other Documents (include Author, Title, Date, and Place of Publication)

Examiner Initial	Desig. ID	Document
<i>J</i>	AQ	A. Ourmazd, "Gettering of Impurities in Silicon," Materials Research Society, Vol. 59, 1986, pp.331-340.
<i>J</i>	AR	A. Ourmazd, et al., "Gettering of Metallic Impurities in Silicon," Materials Research Society, Vol. 36, 1985, pp. 25-30.
<i>J</i>	AS	Etienne G. Colas, et al., "Quantitative Study of Metal Gettering in Silicon," Materials Research Society, Vol. 59, 1986, pp. 341-346.
<i>J</i>	AT	K. Graff et al., "Palladium Test: A Tool to Evaluate Gettering Efficiency," Materials Research Society, Vol. 36, 1985, pp. 19-24.

Examiner Signature

Date Considered

EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Substitute Disclosure Form (PTO-1449)